Syllabus [2025Year 1 Term]

Course Information

Course Title	Semiconductor Processin g and Chemical Engineeri ng	Credits	3
Course Code	346800-1	Required/El ective (For Underg raduate Cou rses)	Selective majors
Department or Major	Department of Chemical E ngineering	Language	English
Methods of Teaching		Lecture Roo m	월9,10,11,12,13,14(3공319)
Time Allotment	Lecture(3) Experiments(0) Trainging & Practice(0) P erformance(0) Designing & Planning(0)	Cyber Lectu res	
Course Type	offline		

Lecturer

	Name	Soohwan Jan	Rank	Professor	Final Acade mic Degree	공학박사
Lect	Department & college	Semiconductor Specialized Work force Training Project Group		Office	College of Engineering - Buildin g 3 510	
urer	Office Phon e Number	031-8005-3623		e-mail	jangmountain@d	ankook.ac.kr
	Field of Inter					

Course Summary

Course Description	Introduce nano-electronic processing and basic electronic as well as optical devices to the non-electrical engineering students. The course will cover materials growth, photolithography, vacuum, vacuum gage, pump, etching, metal and dielectric deposition, device concept and device characterization.
Description Related Courses	Genral chemistry, Physical chemistry, Organic chemistry
Course Goals	 Understanding of basic semiconductor physics. Understanding of semiconductor fabrication processes. Interpretation of operation principle of semiconductor device.
Projected Result	Application of math, basic science, and engineering knowledge. Design of systems, elements, and processed considering limiting conditions.

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	3. Formulating and solving of engineering problems.	
Percentage of th		
e original langua		
ge classes(%)		

Syllabus

Times	Lecture Topic	Lecture Goals	Lecture Methods	Assignments
1	Introduction	Understanding of course goals		
2	Optical lithography	Understanding of O ptical lithography		
3	Optical lithography	Understanding of M ask aligner		
4	Photoresists	Understanding of P ositive / negative P		
5	Vacuum science	Understanding of V acuum pump		
6	Plasmas	Understanding of pl asma principle and generation		
7	Etching	Understanding of W et etching		
8	Etching	Understanding of Dr y etching		
9	Mid. Exam.	Evaluation of cours e achivement		
10	Metalization	Understanding of ev aporator and sputter		
11	Chemical vapordeposition	Understanding of C VD		
12	Diffusion	Understanding of Fu rnace and diffusion model		
13	Device theory	Understanding of Di ode & FET devices		
14	Ion implantation and RTA	Understanding of io n implantation and f ollowing thermal tre atment		
15	Final Exam.	Evaluation of cours e achivement		

Methods of Grading

sequen ce	Description	Percentage	Details
1	Mid-tem Exam	40%	
2	Final-exam	40%	
3	Pop Quizzes	0%	
4	Assignments	0%	
5	Reports	0%	
6	Presentations & Discussions	0%	
7	Attendance	10%	
8		0%	
9	Others	10%	
	All	100%	

Core of Value

핵심가치	전공역량	역량정의	역량구분	값(%)
혁신 (Discovery)	창의적문제해결 (Creative problem-s olving)	주어진 상황과 문제 를 창의적으로 해결 할 수 있는 능력	부역량	30%
혁신 (Discovery)	도전 (Challenging)	전공 지식을 새로운 분야와 융합하고 아 우를 수 있는 능력		0%
혁신 (Discovery)	지식융합 (Knowledge conver gence)	새로운 분야를 개척 하거나 도전적으로 임할 수 있는 능력	주역량	50%
헌신 (Dedication)	세계시민 (Universal value)	세계 공동체 구성원 으로 전공자로서 국 제적 이슈에 대응할 수 있는 능력		0%
헌신 (Dedication)	상호협력 (Cooperation)	공동의 목적 달성을 위해 타인과 상호협 력을 할 수 있는 능력	부역량	20%
헌신 (Dedication)	공동체 (Sense of communit y)	공동체의 구성원으로 서 필요한 태도와 윤 리의식을 가질 수 있 는 능력		0%
능동 (self- Determinatio n)	자기주도 (Self-Managing)	주어진 상황과 문제 를 주도적이고 능동 적으로 해결할 수 있 는 능력		0%
능동 (self- Determinatio n)	지식활용 (Knowledge applica tion)	주어진 상황과 문제에 대해 논리적으로 파악하고 분석할 수 있는 능력		0%

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핵심가치	전공역량	역량정의	역량구분	값(%)
능동 (self- Determinatio n)	논리적사고 (Logical thinking)	전공관련 지식을 필 요에 따라 다양하게 적용하고 활용할 수 있는 능력		0%
능동 (self- Determinatio n)	의사소통 (Articulation)	대화를 통해 다양한 의견을 조율하고 합 의를 이끌어 낼 수 있 는 능력		0%

Textbook(s) & References

Descrip tion	Title	Author	Publisher
Refer ence s	fabrication engineering at the micro and na noscale	STEPHE N A. CA MPBEL L	Oxford University press

Memo

- 1. The lecture will be conducted based on the lecture notes.
- 2. Students are expected to do their best on each exam and are strictly prohibited from any form of cheating.
- 3. Three instances of tardiness will be considered as one absence.